TRANSFER-MOLD TYPE INSULATED TYPE

PS21767



INTEGRATED POWER FUNCTIONS

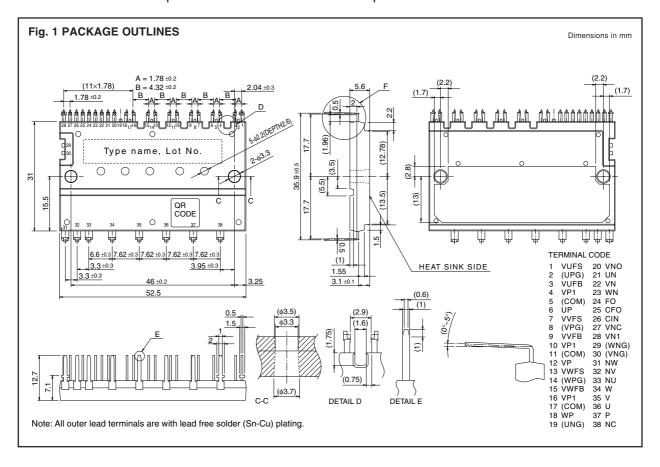
600V/30A low-loss CSTBTTM inverter bridge with N-side three-phase output DC-to-AC power conversion

INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS

- For upper-leg IGBTs: Drive circuit, High voltage high-speed level shifting, Control supply under-voltage (UV) protection.
- For lower-leg IGBTs: Drive circuit, Control supply under-voltage protection (UV), Short circuit protection (SC).
- Fault signaling : Corresponding to an SC fault (Lower-leg IGBT) or a UV fault (Lower-side supply).
- Input interface : 3, 5V line (High Active)
- UL Approved: Yellow Card No. E80276

APPLICATION

AC100V~200V three-phase inverter drive for small power motor control.





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MAXIMUM RATINGS (Tj = 25° C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P-NU, NV, NW	450	V
VCC(surge)	Supply voltage (surge)	Applied between P-NU, NV, NW	500	V
VCES	Collector-emitter voltage		600	V
±IC	Each IGBT collector current	Tc = 25°C	30	Α
±ICP	Each IGBT collector current (peak)	Tc = 25°C, less than 1ms	60	Α
Pc	Collector dissipation	Tc = 25°C, per 1 chip	90.9	W
Tį	Junction temperature		-20~+150	°C

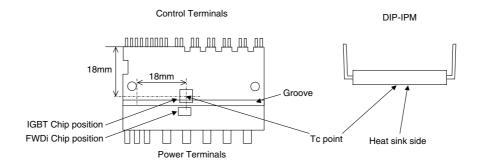
CONTROL (PROTECTION) PART

Symbol	Parameter	Condition	Ratings	Unit
VD	Control supply voltage	Applied between VP1-VNC, VN1-VNC	20	V
VDB	Control supply voltage	Applied between VUFB-VUFS, VVFB-VVFS, VWFB-VWFS 20		V
VIN	Input voltage	Applied between UP, VP, WP, UN, VN, WN-VNC	-0.5~VD+0.5	V
VFO	Fault output supply voltage	Applied between Fo-VNC	-0.5~VD+0.5	V
IFO	Fault output current	Sink current at Fo terminal	1	mA
Vsc	Current sensing input voltage	Applied between CIN-VNC	-0.5~VD+0.5	V

TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Self protection supply voltage limit (short circuit protection capability)	$VD = 13.5 \sim 16.5 V$, Inverter part $T_j = 125 ° C$, non-repetitive, less than 2 μs	400	V
Tc	Module case operation temperature	(Note 1)	− 20~+100	°C
Tstg	Storage temperature		− 40~+125	°C
Viso	Isolation voltage	60Hz, Sinusoidal, AC 1 minute, All pins to heat-sink plate	2500	Vrms

Note 1 : Tc measurement point





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THERMAL RESISTANCE

0	Davamatav	Condition	Limits			Limit
Symbol Parameter		Condition		Тур.	Max.	Unit
Rth(j-c)Q	Junction to case thermal	Inverter IGBT part (per 1/6 module)	_	_	1.1	°C/W
Rth(j-c)F	resistance (Note 2)	Inverter FWD part (per 1/6 module)	_	_	2.8	°C/W

Note 2 : Grease with good thermal conductivity should be applied evenly with about $+100\mu m^{\sim} + 200\mu m$ on the contacting surface of DIP-IPM

and heat-sink.

The contacting thermal resistance between DIP-IPM case and heat sink (Rth(c-f)) is determined by the thickness and the thermal conductivity of the applied grease. For reference, Rth(c-f) (per 1/6 module) is about 0.3°C/W when the grease thickness is 20µm and the thermal conductivity is 1.0W/m·k

ELECTRICAL CHARACTERISTICS ($T_j = 25^{\circ}C$, unless otherwise noted) **INVERTER PART**

Cumple of	Davamatav	Condition		Limits			Unit
Symbol	Parameter			Min.	Тур.	Max.	Unit
VCE(cot)	Collector-emitter saturation $VD = VDB = 15V$ $IC = 30A, T_j = 25^{\circ}C$		_	1.60	2.10	V	
VCE(sat) voltage	VIN = 5V	Ic = 30A, Tj = 125°C	_	1.70	2.20	V	
VEC	FWDi forward voltage	Tj = 25°C, -IC = 30A, VIN = 0V		_	1.50	2.00	V
ton				0.70	1.30	1.90	μs
trr		VCC = 300V, VD = VDB = 15V		_	0.30	_	μs
tc(on)	Switching times	IC = 30A, Tj = 125°C, VIN = $0 \leftrightarrow 5V$		_	0.50	0.80	μs
toff		Inductive load (upper-lov	Inductive load (upper-lower arm)		1.50	2.10	μs
tc(off)		, , ,		_	0.40	0.60	μs
ICES	Collector-emitter cut-off		Tj = 25°C	_	_	1	mA
ICES	current	VCE = VCES	Tj = 125°C	_	_	10	IIIA

CONTROL (PROTECTION) PART

Symbol	Parameter	neter Condition			Limits			
Symbol	Parameter		Con	aition	Min.	Тур.	Max.	Unit
		VD = VDB = 15V Total of		VP1-VNC, VN1-VNC	_	_	7.00	mA
ID.	Circuit current	VIN = 5V	VUFB-V	UFS, VVFB-VVFS, VWFB-VWFS	_	_	0.55	mA
טו	Circuit current	VD = VDB = 15V	Total of	VP1-VNC, VN1-VNC	_	_	7.00	mA
		VIN = 0V	VUFB-V	UFS, VVFB-VVFS, VWFB-VWFS	_	_	0.55	mA
VFOH	Fault output voltage	Vsc = 0V, Fo terminal pull-up to 5V with $10k\Omega$			4.9	_	_	V
VFOL	Fault output voltage	VSC = 1V, IFO = 1mA				_	0.95	V
VSC(ref)	Short circuit trip level	$T_j = 25^{\circ}C, V_D = 15V$ (Note 3)			0.43	0.48	0.53	V
lin	Input current	VIN = 5V			1.0	1.5	2.0	mA
UVDBt				Trip level	10.0	_	12.0	V
UVDBr	Control supply under-voltage	 T _i ≤ 125°C		Reset level	10.5	_	12.5	V
UVDt	protection	1] ≤ 125 C	Trip level	10.3	_	12.5	V	
UVDr				Reset level	10.8	_	13.0	V
tFO	Fault output pulse width	CFO = 22nF		(Note 4)	1.0	1.8	_	ms
Vth(on)	ON threshold voltage	Applied between UP, VP, WP, UN, VN, WN-VNC			_	2.3	2.6	V
Vth(off)	OFF threshold voltage				0.8	1.4	_	V
Vth(hys)	ON/OFF threshold hysteresis voltage				0.5	0.9	_	V

Note 3: Short circuit protection is functioning only at the low-arms. Please select the external shunt resistance such that the SC trip-level is less than 2.0 times of the current rating.



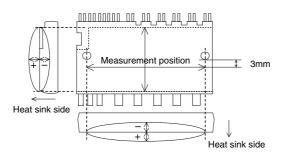
^{4:} Fault signal is output when the low-arms short circuit or control supply under-voltage protective functions works. The fault output pulsewidth tFO depends on the capacitance of CFO according to the following approximate equation: CFO = 12.2 × 10⁻⁶ × tFO [F].

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MECHANICAL CHARACTERISTICS AND RATINGS

Davamatar	Condition		Limits			Llmia
Parameter	00	Min.	Тур.	Max.	Unit	
Mounting torque	Mounting screw : M3 Recommended : 0.78 N·m		0.59	_	0.98	N·m
Weight			_	21	_	g
Heat-sink flatness	(Note 5)		-50	_	100	μm

Note 5: Flatness measurement position



RECOMMENDED OPERATION CONDITIONS

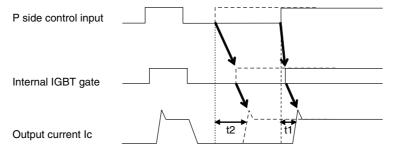
0	Dt	Condition		Recommended valu		value	Unit
Symbol	Parameter	Condition	1	Min.	Тур.	Max.	Unit
Vcc	Supply voltage	Applied between P-NU, NV, NW	'	0	300	400	V
VD	Control supply voltage	Applied between VP1-VNC, VN1-	Vnc	13.5	15.0	16.5	V
VDB	Control supply voltage	Applied between VUFB-VUFS, VV	FB-VVFS, VWFB-VWFS	13.0	15.0	18.5	V
ΔV D, ΔV DB	Control supply variation			-1	_	1	V/µs
tdead	Arm shoot-through blocking time	For each input signal, Tc ≤ 100°0	0	2	_	_	μs
fPWM	PWM input frequency	T _c ≤ 100°C, T _j ≤ 125°C		_	_	20	kHz
	Output r.m.s. current	VCC = 300V, VD = VDB = 15V,	fPWM = 5kHz	_	_	21	
lo		P.F = 0.8, sinusoidal PWM $T_c \le 100^{\circ}C$, $T_i \le 125^{\circ}C$ (Note 6)	fPWM = 15kHz	_	_	16	Arms
PWIN(on)			(Note 7)	0.3	_	_	
		200 ≤ VCC ≤ 350V, 13.5 ≤ VD ≤ 16.5V,	Below rated current	1.5	_	_	
PWIN(off)	Minimum input pulse width	$13.0 \le VDB \le 18.5V$, $-20^{\circ}C \le T_c \le 100^{\circ}C$,	Between rated current and 1.7 times of rated current	3.0	_	_	μs
		N-line wiring inductance less than 10nH (Note 8)	Between 1.7 times and 2.0 times of rated current	3.6	_	_	
VNC	VNC voltage variation	Between VNC-NU, NV, NW (including surge)			_	5.0	V
Tj	Junction temperature			-20	_	125	°C



Note 6: The allowable r.m.s. current value depends on the actual application conditions.
7: Input signal with ON pulse width less than PWIN(on) might make no response.
8: IPM might make delayed response (less than about 2µsec) or no response for the input signal with off pulse width less than PWIN(off). Please refer Fig. 2 about delayed response and Fig. 6 about N-line inductance.

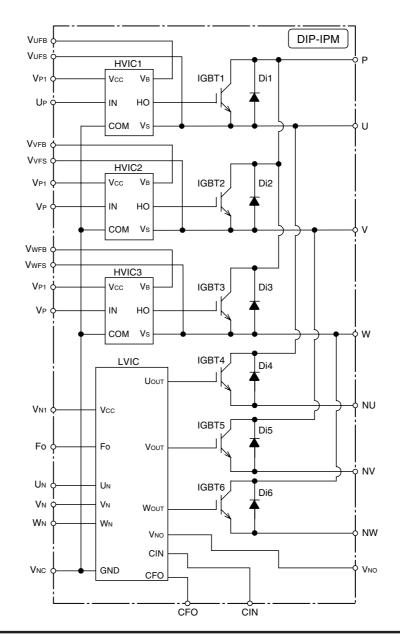
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Fig. 2 ABOUT DELAYED RESPONSE AGAINST SHORTER INPUT OFF SIGNAL THAN PWIN (off) (P side only)



Real line ··· off pulse width > PWIN(off) : turn on time t1 Broken line ··· off pulse width < PWIN(off) : turn on time t2

Fig. 3 THE DIP-IPM INTERNAL CIRCUIT



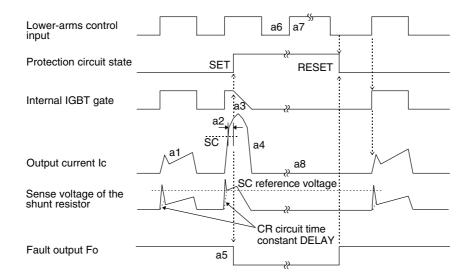


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Fig. 4 TIMING CHARTS OF THE DIP-IPM PROTECTIVE FUNCTIONS

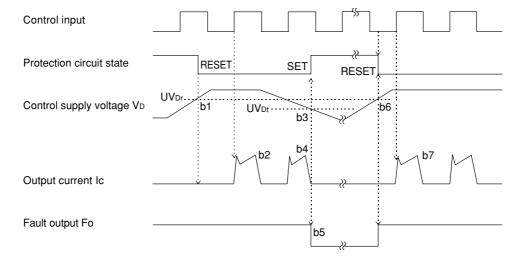
[A] Short-Circuit Protection (Lower-arms only with the external shunt resistor and CR filter)

- a1. Normal operation: IGBT ON and carrying current.
- a2. Short circuit current detection (SC trigger).
- a3. IGBT gate hard interruption.
- a4. IGBT turns OFF.
- a5. Fo timer operation starts: The pulse width of the Fo signal is set by the external capacitor CFo.
- a6. Input "L": IGBT OFF.
- a7. Input "H"
- a8. IGBT OFF state in spite of input "H".



[B] Under-Voltage Protection (Lower-arm, UVD)

- b1. Control supply voltage rising: After the voltage level reaches UVDr, the circuits start to operate when next input is applied. b2. Normal operation: IGBT ON and carrying current.
- b3. Under voltage trip (UVDt).
- b4. IGBT turns OFF in spite of control input condition.
- b5. Fo operation starts.
- b6. Under voltage reset (UVDr).
- b7. Normal operation: IGBT ON and carrying current.





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[C] Under-Voltage Protection (Upper-arm, UVDB)

- c1. Control supply voltage rises: After the voltage level reaches UVDBr, the circuits start to operate. c2. Protection circuit state reset: IGBT ON and carrying current.
- c3. Normal operation: IGBT ON and carrying current.
- c4. Under-voltage trip (UVDBt).c5. IGBT OFF inspite of control input condition, but there is no Fo signal output.
- c6. Under-voltage reset (UVDBr).
- c7. Normal operation: IGBT ON and carrying current.

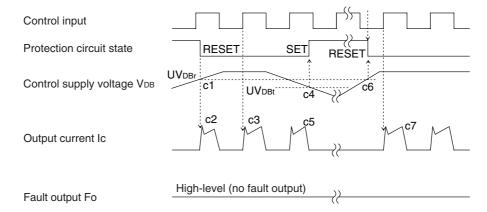
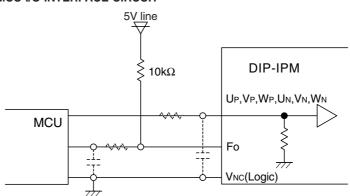
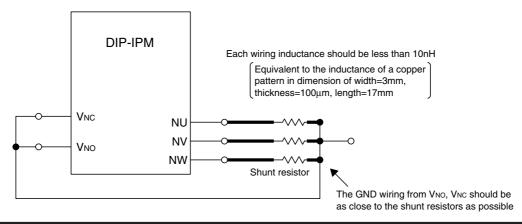


Fig. 5 RECOMMENDED MCU I/O INTERFACE CIRCUIT



Note: RC coupling at each input (parts shown dotted) may change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The DIP-IPM input signal section integrates a 2.5kΩ(min) pull-down resistor. Therefore, when using a external filtering resistor, care must be taken to satisfy the turn-on threshold voltage requirement.

Fig. 6 RECOMMENDED WIRING AROUND THE SHUNT RESISTOR

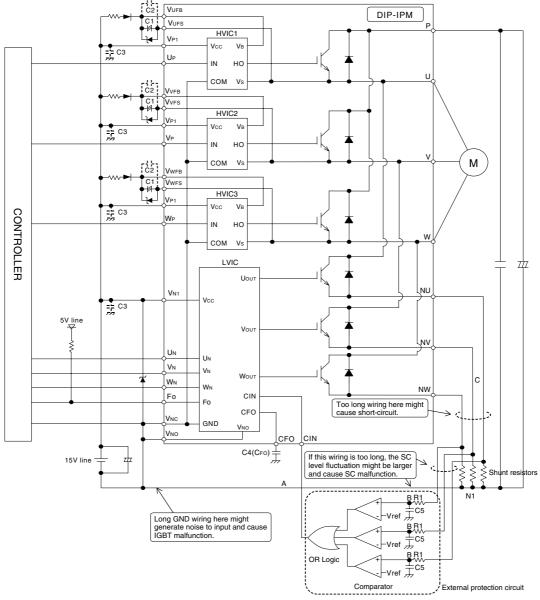




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Fig. 7 TYPICAL DIP-IPM APPLICATION CIRCUIT EXAMPLE

C1: Tight tolerance temp-compensated electrolytic type C2,C3: 0.22~2µF R-category ceramic capacitor for noise filtering



- Note 1 : Input drive is High-active type. There is a 2.5kΩ(Min.) pull-down resistor integrated in the IC input circuit. To prevent malfunction, the wiring of each input should be as short as possible. When using RC coupling circuit, make sure the input signal level meet the turn-on and turn-off threshold voltage.
 - : Thanks to HVIC inside the module, direct coupling to MCU without any opto-coupler or transformer isolation is possible.
 - : Fo output is open drain type. It should be pulled up to the positive side of a 5V power supply by a resistor of about 10kΩ Fo output pulse width is determined by the external capacitor (CFo) between CFO and VNC terminals (e.g CFo = 22nF → tFo = 1.8ms (tvp.))

 - : To prevent erroneous protection, the wiring of A, B should be as short as possible.
 : The time constant R1C5 of the protection circuit should be selected in the range of 1.5-2μs. SC interrupting time might vary with the wiring pattern. Tight tolerance, temp-compensated type is recommended for R1, C5.
 - : All capacitors should be mounted as close to the terminals of the DIP-IPM as possible. (C1: good temperature, frequency characteristic electrolytic type, and C2, C3: good temperature, frequency and DC bias characteristic ceramic type are recommended.)
 - 7 : To prevent surge destruction, the wiring between the smoothing capacitor and the P, N1 terminals should be as short as possible. Generally a 0.1-0.22μF snubber between the P-N1 terminals is recommended.
 - : It is recommended to insert a Zener diode (24V/1W) between each pair of control supply terminals to prevent surge destruction.
 - : If control GND is connected to power GND by broad pattern, it may cause malfunction by power GND fluctuation. It is recommended to connect control GND and power GND at only a point.
 - 10: The reference voltage Vref of comparator should be set up the same rating of short circuit trip level (Vsc(ref): min.0.43V to max.0.53V).
 - 11 : OR logic output high level should exceed the maximum short circuit trip level (Vsc(ref): max.0.53V).

